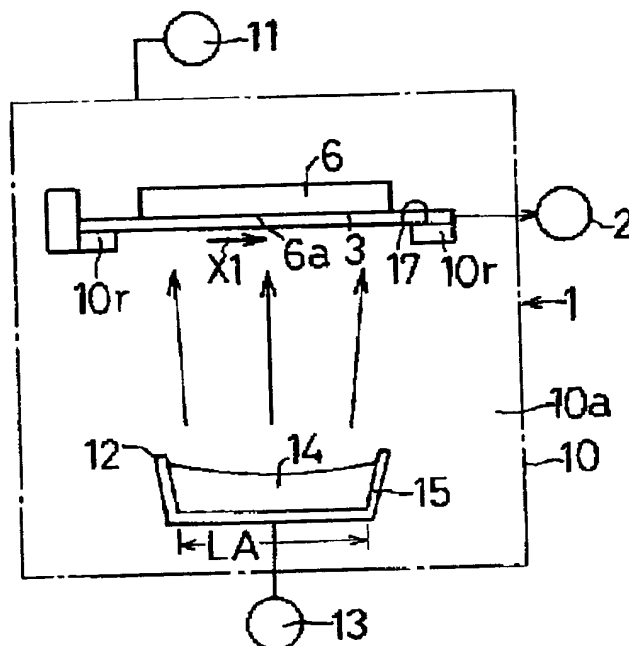


Patent Abstracts of Japan

TITLE : FORMATION OF THIN FILM



SOLUTION: A mask 3 having plural openings and a substrate 6 having the face 6a to be film-formed is used, and, in a stage in which the mask 3 is confronted with the face 6a to be film-formed, the face 6a to be film-formed is applied with film forming treatment of a thin film so as to transfer the shapes of the openings of the mask 3. The film forming treatment is executed in a state in which the mask 3 is applied with tension so as to suppress the warpage and deflection of the mask 3. The mask may have a double structure. Furthermore, the mask can be adhered to the face 6a to be film-formed in the substrate 6 by the magnetic attraction. It can be utilized for thin film formation in an organic EL element.

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